

<b>Notice of References Cited</b>	Application/Control No. 10/025,331	Applicant(s)/Patent Under Reexamination BOUCHARD ET AL.	
	Examiner Bao Q Truong	Art Unit 2187	Page 1 of 1

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	C	US-4,912,698	03-1990	Bitzinger et al.	370/244
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	U	Davis et al., The New DRAM Interfaces: SDRAM, DRDRAM and Variants, Oct. 2000, High Performance Computing, 3 <sup>rd</sup> ed. Int Symp.
	V	Sato et al., Fast Cycle RAM (FCRAM); a 20-ns Random Row Access, Pipe-Lined Operating DRAM, 1998, Symp. on VLSI Circuits Digest of Technical Papers.
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.